

Schottky Diode

V_{RRM} = 45 V
 I_{FAV} = 2x 30 A
 V_F = 0.45 V

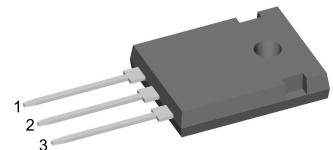
High Performance Schottky Diode

Low Loss and Soft Recovery

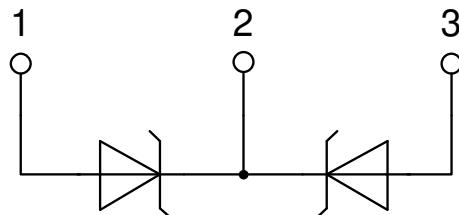
Common Cathode

Part number

DSSK60-0045B



Backside: cathode



Features / Advantages:

- Very low V_F
- Extremely low switching losses
- Low I_{rm} values
- Improved thermal behaviour
- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching

Applications:

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

Package: TO-247

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

Disclaimer Notice

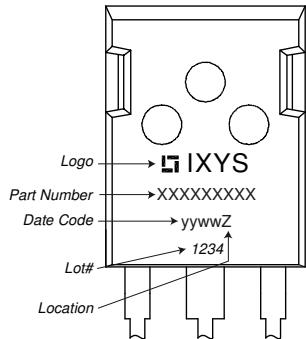
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Schottky

Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^\circ C$			45	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^\circ C$			45	V
I_R	reverse current, drain current	$V_R = 45 V$ $V_R = 45 V$	$T_{VJ} = 25^\circ C$ $T_{VJ} = 100^\circ C$		40 200	mA
V_F	forward voltage drop	$I_F = 30 A$ $I_F = 60 A$ $I_F = 30 A$ $I_F = 60 A$	$T_{VJ} = 25^\circ C$ $T_{VJ} = 125^\circ C$		0.50 0.68 0.45 0.66	V
I_{FAV}	average forward current	$T_C = 125^\circ C$ rectangular $d = 0.5$	$T_{VJ} = 150^\circ C$		30	A
V_{F0} r_F	threshold voltage slope resistance } for power loss calculation only		$T_{VJ} = 150^\circ C$		0.24 6.5	V mΩ
R_{thJC}	thermal resistance junction to case				1.1	K/W
R_{thCH}	thermal resistance case to heatsink			0.25		K/W
P_{tot}	total power dissipation		$T_C = 25^\circ C$		115	W
I_{FSM}	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}; V_R = 0 V$	$T_{VJ} = 45^\circ C$		640	A
C_J	junction capacitance	$V_R = 5 V$ $f = 1 \text{ MHz}$	$T_{VJ} = 25^\circ C$		1.94	nF
E_{AS}	non-repetitive avalanche energy	$I_{AS} = 28 A$ $L = 180 \mu H$	$T_{VJ} = 25^\circ C$		112	mJ
I_{AR}	repetitive avalanche current	$V_A = 1.5 \cdot V_R$ typ. $f = 10 \text{ kHz}$			2.8	A

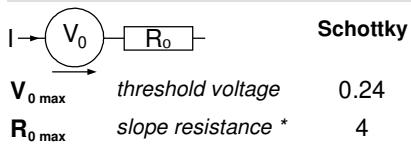
Package TO-247

Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal ¹⁾			70	A
T_{VJ}	virtual junction temperature		-55		150	°C
T_{op}	operation temperature		-55		125	°C
T_{stg}	storage temperature		-55		150	°C
Weight				6		g
M_d	mounting torque		0.8		1.2	Nm
F_c	mounting force with clip		20		120	N

Product Marking


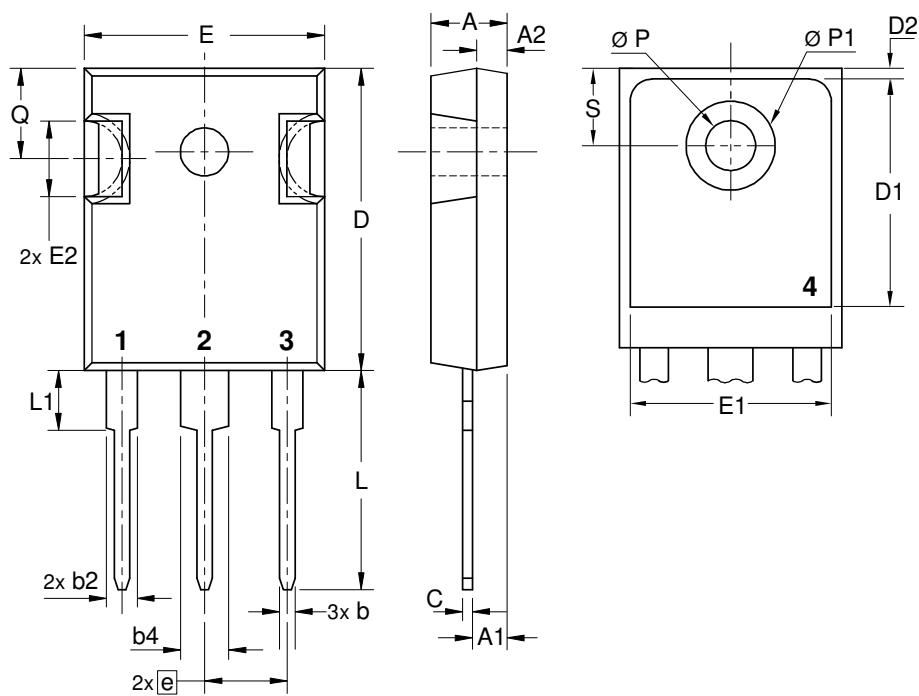
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSSK60-0045B	DSSK60-0045B	Tube	30	501501

Equivalent Circuits for Simulation
^{*}on die level

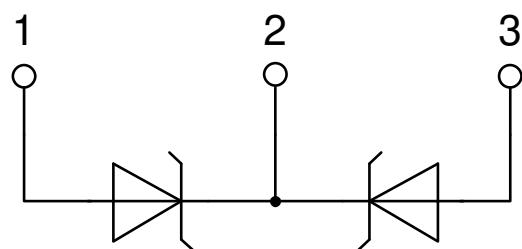
 $T_{VJ} = 150^\circ\text{C}$


V

mΩ

Outlines TO-247


Sym.	Inches min. max.	Millimeter min. max.
A	0.185 0.209	4.70 5.30
A1	0.087 0.102	2.21 2.59
A2	0.059 0.098	1.50 2.49
D	0.819 0.845	20.79 21.45
E	0.610 0.640	15.48 16.24
E2	0.170 0.216	4.31 5.48
e	0.215 BSC	5.46 BSC
L	0.780 0.800	19.80 20.30
L1	- 0.177	- 4.49
Ø P	0.140 0.144	3.55 3.65
Q	0.212 0.244	5.38 6.19
S	0.242 BSC	6.14 BSC
b	0.039 0.055	0.99 1.40
b2	0.065 0.094	1.65 2.39
b4	0.102 0.135	2.59 3.43
c	0.015 0.035	0.38 0.89
D1	0.515 -	13.07 -
D2	0.020 0.053	0.51 1.35
E1	0.530 -	13.45 -
Ø P1	- 0.29	- 7.39



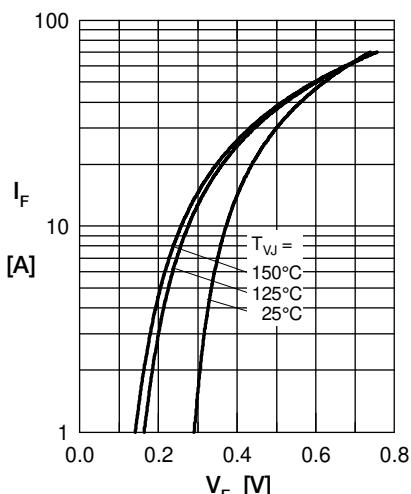
Schottky


Fig. 1 Max. forward voltage drop characteristics

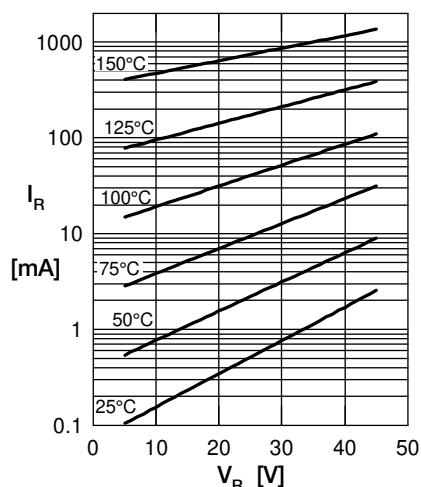


Fig. 2 Typ. reverse current I_R vs. reverse voltage V_R

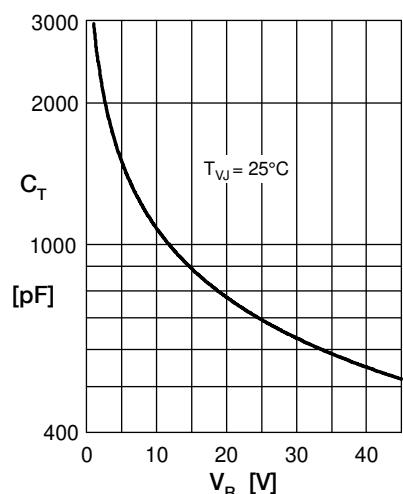


Fig. 3 Typ. junction capacitance C_T vs. reverse voltage V_R

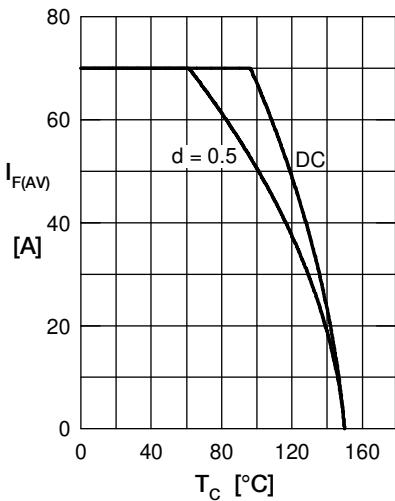


Fig. 4 Average forward current $I_{F(AV)}$ vs. case temp. T_C

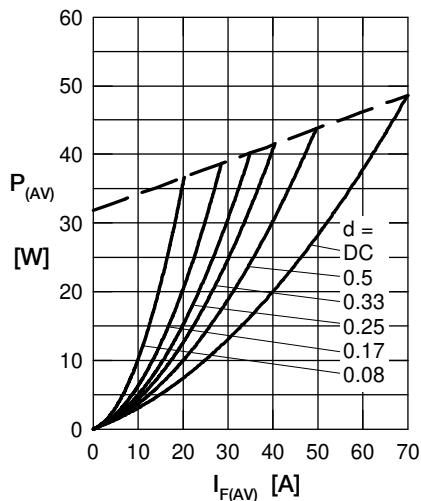


Fig. 5 Forward power loss characteristics

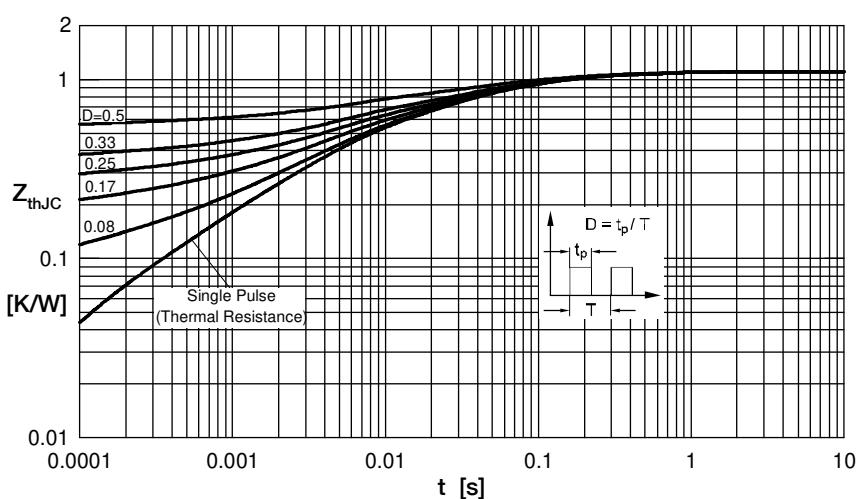


Fig. 6 Transient thermal impedance junction to case at various duty cycles

Note: All curves are per diode